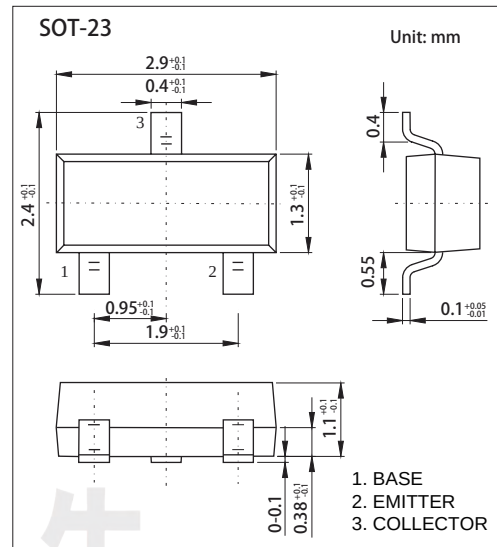


Transistor

PNP Transistors S8550

■ Features

- Collector current: $I_c = -0.5A$
- Complementary to S8050



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-25	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_c	-500	mA
Collector Power Dissipation	P_c	300	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	

Transistor

PNP Transistors S8550

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	VCBO	IC= -100 μ A, IE=0	-40			V
Collector- emitter breakdown voltage	VCEO	IC= -1 mA, IB=0	-25			
Emitter - base breakdown voltage	VEBO	IE= -100 μ A, IC=0	-5			
Collector cut-off current	ICBO	VCB= -40 V, IE=0			-0.1	μ A
Collector cut-off current	ICEO	VCE= -20 V, IB=0			-0.1	
Emitter cut-off current	IEBO	VEB= -3V, IC=0			-0.1	
Collector-emitter saturation voltage	VCE(sat)	IC=-500 mA, IB= -50mA			-0.6	V
Base - emitter saturation voltage	VBE(sat)	IC=-500 mA, IB= -50mA			-1.2	
DC current gain	hFE(1)	VCE= -1V, IC= -50mA	120		400	
	hFE(2)	VCE= -1V, IC= -500mA	50			
Transition frequency	fT	VCE= -6V, IC= -20mA,f=30MHz	150			MHz

■ Classification of hFE(1)

Rank	L	H	J
Range	120-200	200-350	300-400
Marking	2TY		

Transistor

PNP Transistors S8550

■ Typical Characteristics

